

Title (en)

Cold spray apparatus and method with modulated gasstream

Title (de)

Kaltspritzanlage und Kaltspritzverfahren mit moduliertem Gasstrom

Title (fr)

Appareil et procédé de pulvérisation à froid avec écoulement gazeux module

Publication

EP 1806429 A1 20070711 (DE)

Application

EP 06000403 A 20060110

Priority

EP 06000403 A 20060110

Abstract (en)

The cold gas spray apparatus (1) has a high pressure gas generator (22) for the production of a high pressure gases and a nozzle (8) from which a cold gas particle stream (7) is emitted. An influencing medium (25,26,29,32,35,36) is provided. The cold gas particle stream is guided for variable modification of the characteristics temperature, pressure, particle density, particle material and velocity. A property of the cold gas particle stream is periodically modifiable by influencing medium. An independent claim is also included for a cold gas spraying method by the cold gas spray apparatus.

Abstract (de)

Das Kaltgasspritzverfahren liefert unter Umständen nicht optimale Beschichtungsergebnisse. Das erfindungsgemäße Kaltgasspritzverfahren verwendet Kaltgasströme, die in ihren Eigenschaften (Temperatur (T), Partikeldichte (Ä), Druck (p), Partikelgeschwindigkeit (v)) wechselhaft verändert werden und so den gewünschten Eigenschaften der Beschichtungen angepasst werden können.

IPC 8 full level

C23C 24/04 (2006.01); **B05B 7/22** (2006.01)

CPC (source: EP US)

B05B 1/083 (2013.01 - EP US); **B05B 7/1486** (2013.01 - EP US); **B05B 7/1626** (2013.01 - EP US); **C23C 24/04** (2013.01 - EP US)

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AL BA HR MK YU

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